ALPHA & OMEGA SEMICONDUCTOR

AON6240

40V N-Channel MOSFET

General Description

The AON6240 uses trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance.Power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Crss.In addition,switching behavior is well controlled with a "Schottky style" soft recovery body diode.

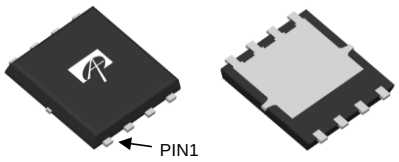
Product Summary

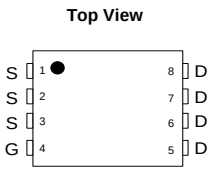
V_{DS}	40V
I_D (at V_{GS}=10V)	85A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 1.6mΩ
$R_{DS(ON)}$ (at V_{GS} = 4.5V)	< 2.4mΩ

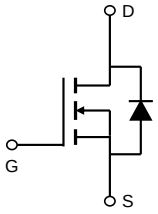
100% UIS Tested
100% R_g Tested

Green Product

DFN5X6







Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [G]	T_C=25°C	I_D	85	A
	T_C=100°C		67	
Pulsed Drain Current [C]		I_{DM}	355	
Continuous Drain Current	T_A=25°C	I_{DSM}	27	A
	T_A=70°C		22	
Avalanche Current [C]		I_{AS}, I_{AR}	82	A
Avalanche energy L=0.1mH [C]		E_{AS}, E_{AR}	336	mJ
Power Dissipation [B]	T_C=25°C	P_D	83	W
	T_C=100°C		33	
Power Dissipation [A]	T_A=25°C	P_{DSM}	2.3	W
	T_A=70°C		1.5	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	14	17	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		40	55	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1	1.5	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	40			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=40V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	1.3	1.9	2.4	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	355			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		1.3	1.6	mΩ
		T_J=125°C		2.1	2.7	
		V_{GS}=4.5V, I_D=20A		1.8	2.4	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		166		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.7	1	V
I_S	Maximum Body-Diode Continuous Current[G]				85	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=20V, f=1MHz	4360	5458	6550	pF
C_{oss}	Output Capacitance		970	1395	1815	pF
C_{rss}	Reverse Transfer Capacitance		30	103	176	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.5	1.0	1.6	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=20V, I_D=20A	58	72.8	88	nC
Q_g(4.5V)	Total Gate Charge		24	31	44	nC
Q_{gs}	Gate Source Charge			14.8		nC
Q_{gd}	Gate Drain Charge			10.8		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=20V, R_L=1Ω, R_{GEN}=3Ω		14.8		ns
t_r	Turn-On Rise Time			5.5		ns
$t_{D(off)}$	Turn-Off DelayTime			61.3		ns
t_f	Turn-Off Fall Time			10		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=500A/µs	16	23.9	31	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=500A/µs	59	84.6	110	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO MAKE CHANGES TO PRODUCT SPECIFICATIONS WITHOUT NOTICE. IT IS THE RESPONSIBILITY OF THE CUSTOMER TO EVALUATE SUITABILITY OF THE PRODUCT FOR THEIR INTENDED APPLICATION. CUSTOMER SHALL COMPLY WITH APPLICABLE LEGAL REQUIREMENTS, INCLUDING ALL APPLICABLE EXPORT CONTROL RULES, REGULATIONS AND LIMITATIONS.

AOS' products are provided subject to AOS' terms and conditions of sale which are set forth at:
http://www.aosmd.com/terms_and_conditions_of_sale

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

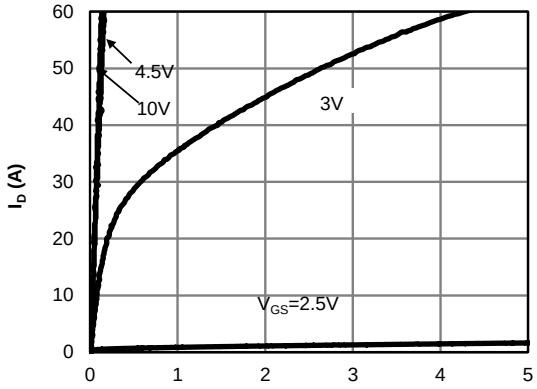


Fig 1: On-Region Characteristics (Note E)

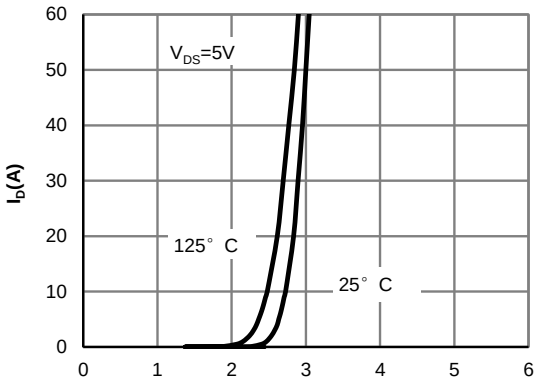


Figure 2: Transfer Characteristics (Note E)

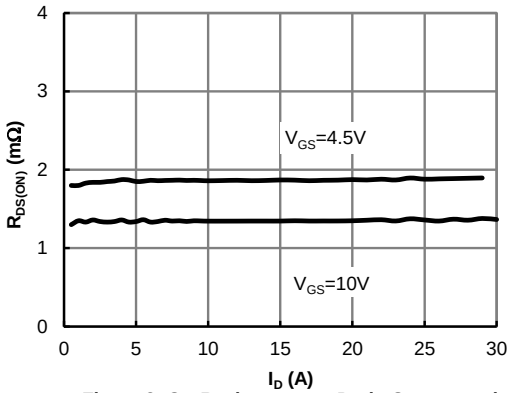


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

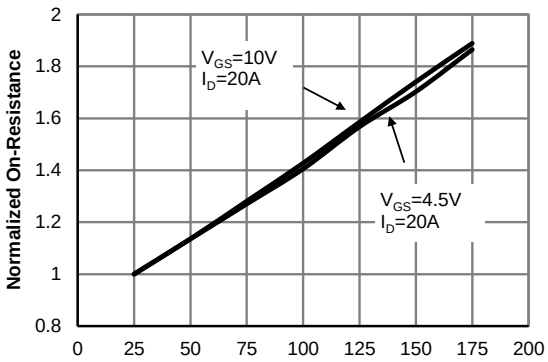


Figure 4: On-Resistance vs. Junction Temperature (Note E)

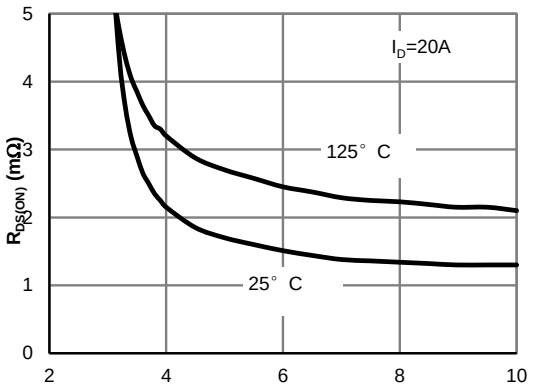


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

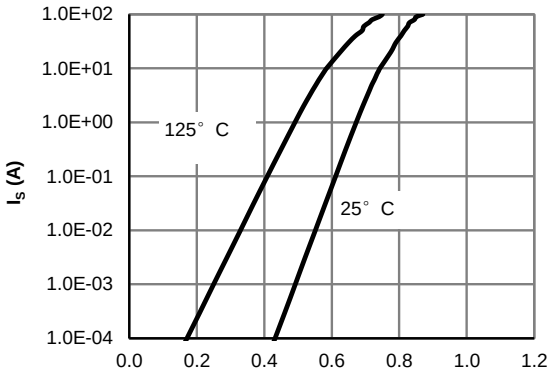


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

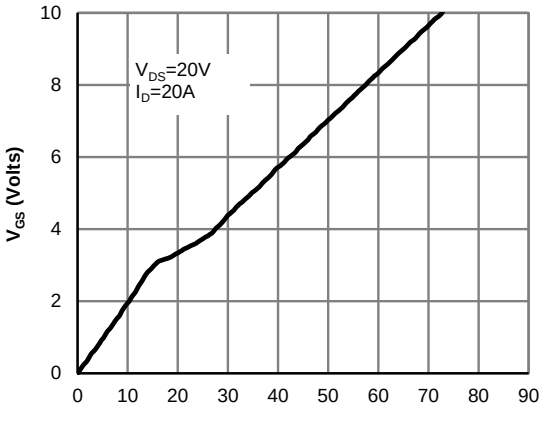


Figure 7: Gate-Charge Characteristics

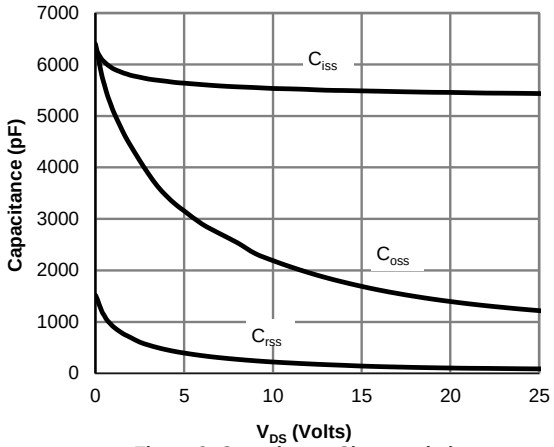


Figure 8: Capacitance Characteristics

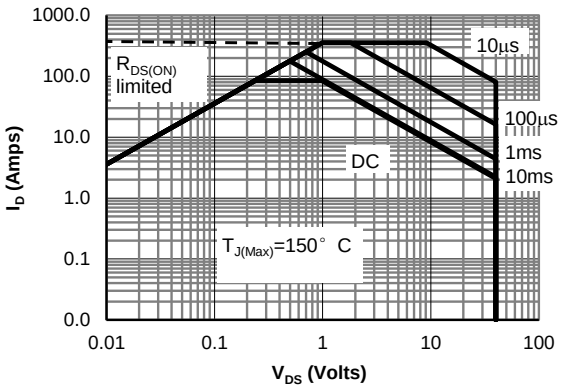


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

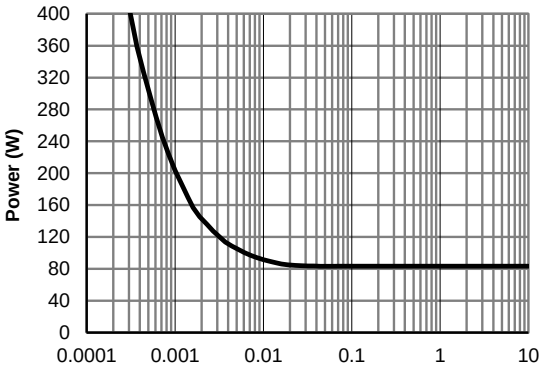


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

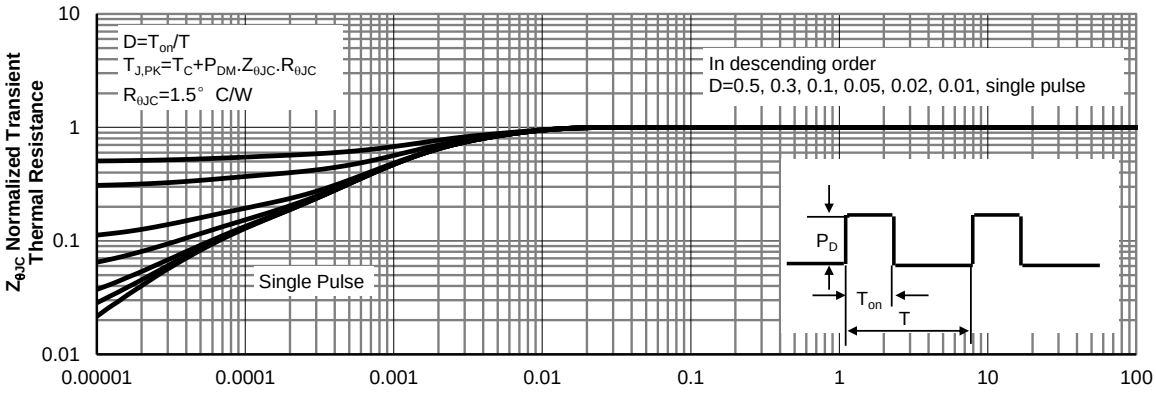


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

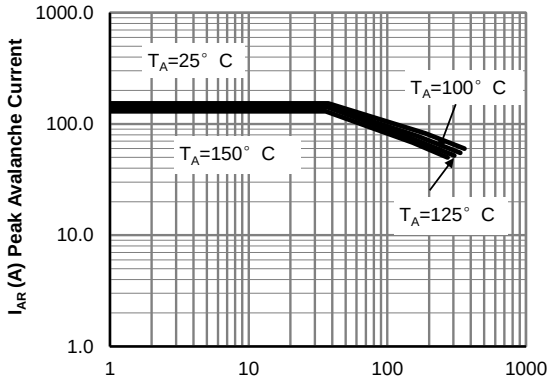


Figure 12: Single Pulse Avalanche capability (Note C)

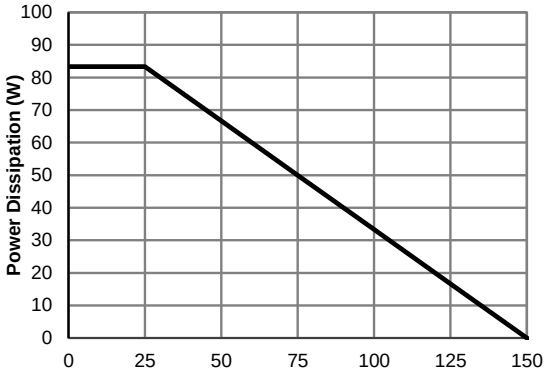


Figure 13: Power De-rating (Note F)

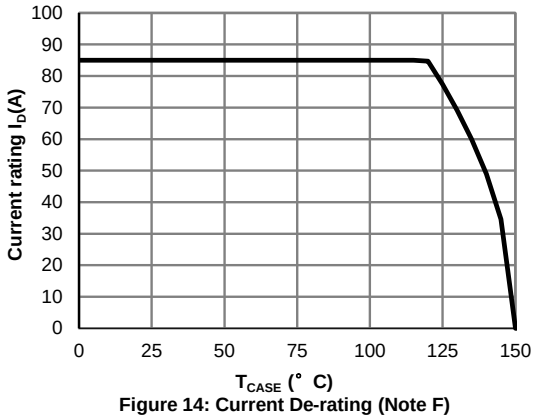


Figure 14: Current De-rating (Note F)

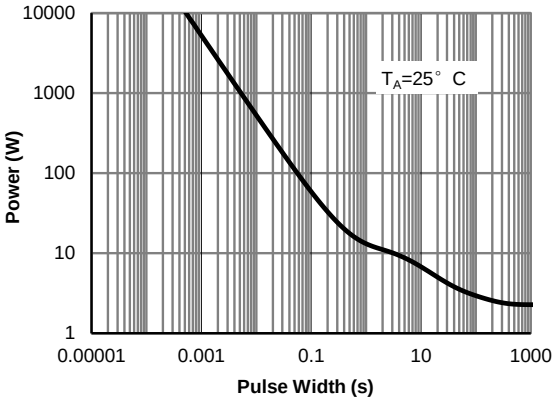


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

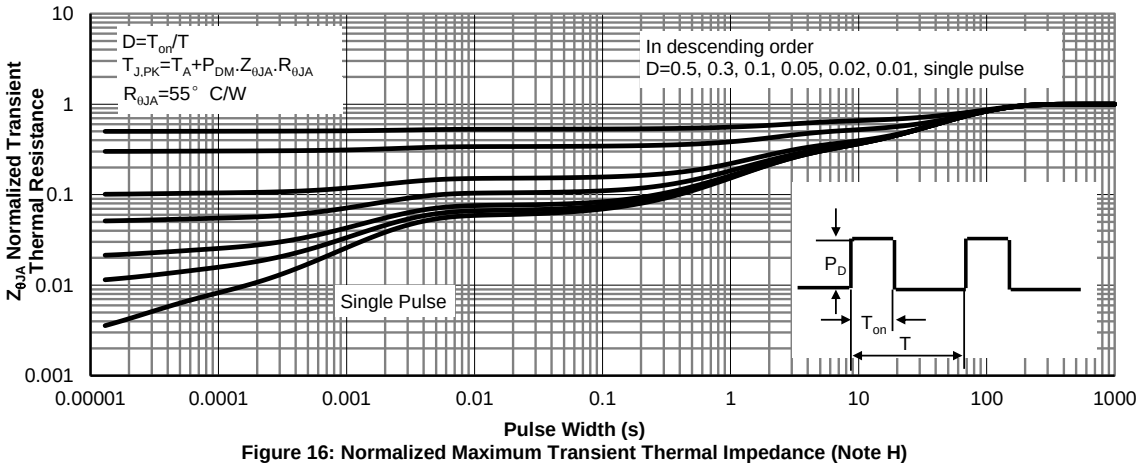
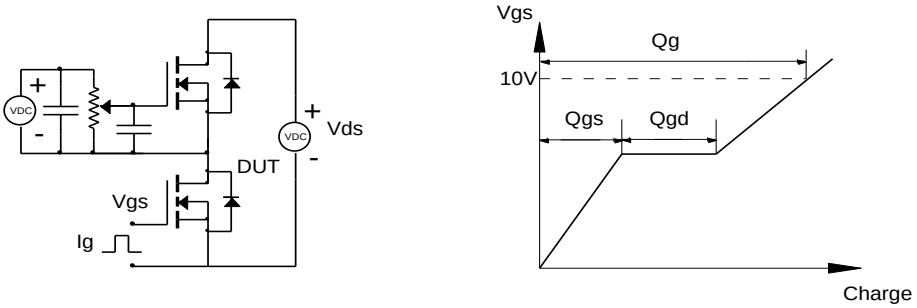
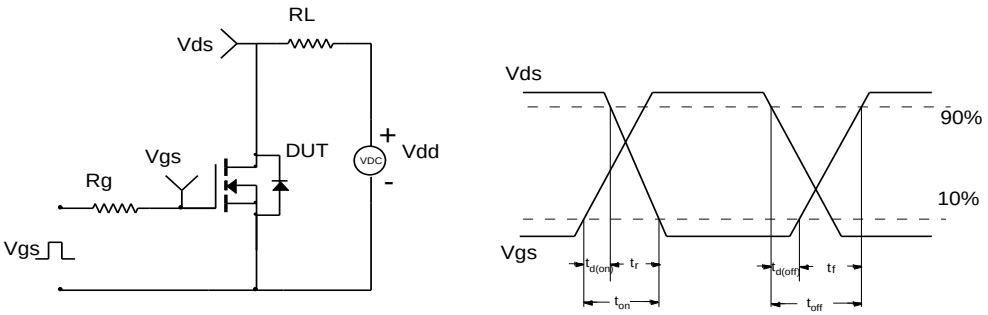


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

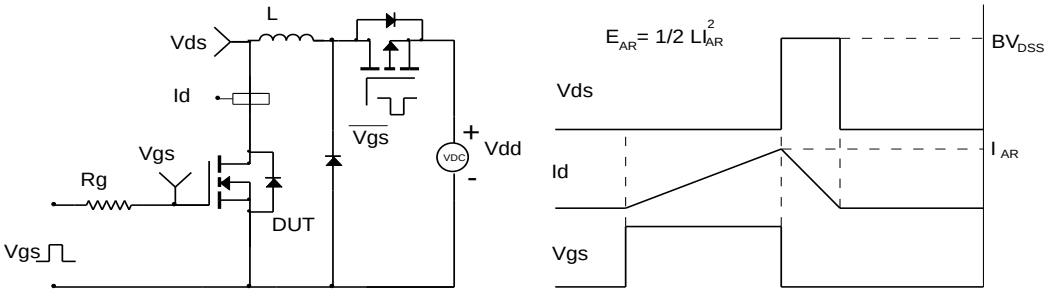
Gate Charge Test Circuit & Waveform



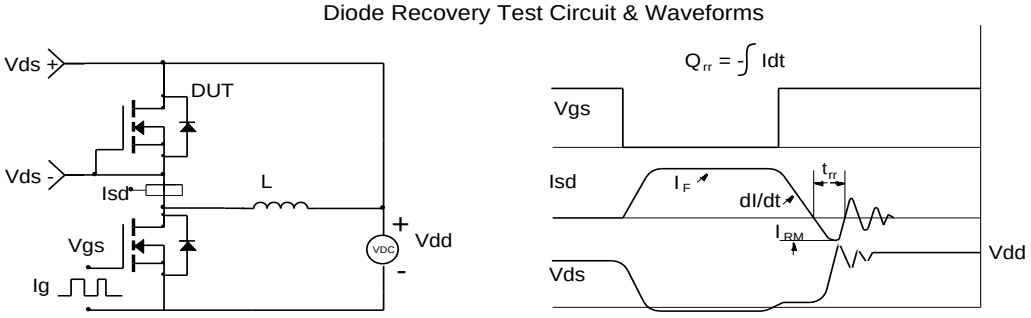
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



ENTEGRECİ

Bu belge www.entegreci.com üzerinden sunulmaktadır.

Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

www.entegreci.com | **destek@entegreci.com** | **0850 305 90 34**

Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

Bu sayfa Entegreci tarafından eklenmiştir. Belgenin önceki sayfaları asıl yayıncısına aittir ve içeriği değiştirilmemiştir; en güncel sürüm için belgenin yayıncısına başvurun.